

AMENDMENTS TO THE SPECIFICATION:

Page 3:

Please substitute the following paragraph for the paragraph beginning at line 16:

As will be described later, a nonvolatile semiconductor memory device that secures a quantity of captured charges is disclosed in, for example, Patent Document 3 (Japanese Patent Application Laid-open No. 5-75133).

Page 23:

Please substitute the following paragraph for the paragraph beginning at line 12:

Japanese Patent Application Laid-open No. 7-75133 5-75133, for example, describes a method of nitriding silicon precipitated in a silicon-rich silicon oxide film and injecting electrons into silicon nitride. However, this method is considered to have the following disadvantages. The silicon-rich silicon oxide film (Si_xO_2 , ($X>1$)) has many traps therein and it is difficult to secure the charge holding characteristic of the memory cell. In addition, it is difficult to provide single layer traps and secure

insulation between the stacked traps. Further, since the thickness of the traps and those of the insulator films located above and below the traps tend to be large, it is difficult to deal with the reduction of a memory cell size. It is considered that the silicon oxide film that covers the silicon nitride dots in this embodiment is Si_xO_2 , where $x \leq 1$.